

FDU3N50NZTU

N-Channel UniFET II MOSFET

500 V, 2.5 A, 2.5 Ω

UniFET II MOSFET is ON Semiconductor's high voltage MOSFET family based on advanced planar stripe and DMOS technology. This advanced MOSFET family has the smallest on-state resistance among the planar MOSFET, and also provides superior switching performance and higher avalanche energy strength. In addition, internal gate-source ESD diode allows UniFET II MOSFET to withstand over 2 kV HBM surge stress. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.

Features

- $R_{DS(on)} = 2.1 \Omega$ (Typ.) @ $V_{GS} = 10$ V, $I_D = 1.25$ A
- Low Gate Charge (Typ. 6.2 nC)
- Low C_{rss} (Typ. 2.5 pF)
- 100% Avalanche Tested
- Improved dv/dt Capability
- ESD Improved Capability
- These Devices are Pb-Free and are RoHS Compliant

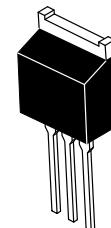
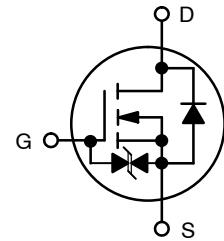
Applications

- LCD / LED TV
- Lighting
- Charger / Adapter



ON Semiconductor®

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IPAK3
CASE 369AR

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 2 of this data sheet.

FDU3N50NZTU

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DSS}	Drain-to-Source Voltage	500	V
V_{GSS}	Gate-to-Source Voltage	± 25	V
I_D	Drain Current	Continuous ($T_C = 25^\circ\text{C}$)	2.5
		Continuous ($T_C = 100^\circ\text{C}$)	1.5
I_{DM}	Drain Current	Pulsed (Note 1)	A
E_{AS}	Single Pulse Avalanche Energy (Note 2)	114	mJ
I_{AR}	Avalanche Current (Note 1)	2.5	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	4	mJ
dv/dt	Peak Diode Recovery (Note 3)	10	V/ns
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	40
		Derate Above 25°C	0.3
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering Purposes (1/8" from case for 5 seconds)	300	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. $L = 36.6 \text{ mH}$, $I_{AS} = 2.5 \text{ A}$, $V_{DD} = 50 \text{ V}$, $R_G = 25 \Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 2.5 \text{ A}$, $di/dt \leq 200 \text{ A/s}$, $V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta,JC}$	Thermal Resistance, Junction-to-Case, Max.	3.1	$^\circ\text{C/W}$
$R_{\theta,JA}$	Thermal Resistance, Junction-to-Ambient, Max.	90	

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDU3N50NZTU	FDU3N50NZ	IPAK	Tube	N/A	N/A	75 units

FDU3N50NZTU

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

BV_{DSS}	Drain-to-Source Breakdown Voltage	$I_D = 250 \mu\text{A}$, $V_{\text{GS}} = 0 \text{ V}$, $T_C = 25^\circ\text{C}$	500	—	—	V
$\Delta \text{BV}_{\text{DSS}/\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C	—	0.5	—	$^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}} = 500 \text{ V}$, $V_{\text{GS}} = 0 \text{ V}$	—	—	1	μA
		$V_{\text{DS}} = 400 \text{ V}$, $V_{\text{GS}} = 0 \text{ V}$, $T_C = 125^\circ\text{C}$	—	—	10	
I_{GSS}	Gate-to-Body Leakage Current	$V_{\text{GS}} = \pm 25 \text{ V}$, $V_{\text{DS}} = 0 \text{ V}$	—	—	± 10	μA

ON CHARACTERISTICS

$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{GS}} = V_{\text{DS}}$, $I_D = 250 \mu\text{A}$	3.0	—	5.0	V
$R_{\text{DS(on)}}$	Static Drain-to-Source On Resistance	$V_{\text{GS}} = 10 \text{ V}$, $I_D = 1.25 \text{ A}$	—	2.1	2.5	Ω
g_{FS}	Forward Transconductance	$V_{\text{DS}} = 20 \text{ V}$, $I_D = 1.25 \text{ A}$	—	1.9	—	S

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{\text{DS}} = 25 \text{ V}$, $V_{\text{GS}} = 0 \text{ V}$, $f = 1 \text{ MHz}$	—	210	280	pF
C_{oss}	Output Capacitance		—	30	45	
C_{rss}	Reverse Transfer Capacitance		—	2.5	5	
$Q_{\text{g(tot)}}$	Total Gate Charge at 10 V	$V_{\text{DS}} = 400 \text{ V}$, $I_D = 2.5 \text{ A}$, $V_{\text{GS}} = 10 \text{ V}$ (Note 4)	—	6.2	8	nC
Q_{gs}	Gate-to-Source Gate Charge		—	1.4	—	
Q_{gd}	Gate-to-Drain "Miller" Charge		—	3.1	—	

SWITCHING CHARACTERISTICS

$t_{\text{d(on)}}$	Turn-On Delay Time	$V_{\text{DD}} = 250 \text{ V}$, $I_D = 2.5 \text{ A}$, $V_{\text{GS}} = 10 \text{ V}$, $R_G = 25 \Omega$ (Note 4)	—	10	30	ns
t_r	Turn-On Rise Time		—	15	40	
$t_{\text{d(off)}}$	Turn-Off Delay Time		—	26	60	
t_f	Turn-Off Fall Time		—	17	45	

DRAIN-SOURCE DIODE CHARACTERISTICS

I_S	Maximum Continuous Drain to Source Diode Forward Current	—	—	2.5	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	—	—	10		
V_{SD}	Drain to Source Diode Forward Voltage	$V_{\text{GS}} = 0 \text{ V}$, $I_{\text{SD}} = 2.5 \text{ A}$	—	—	1.4	V
t_{rr}	Reverse Recovery Time	$V_{\text{GS}} = 0 \text{ V}$, $I_{\text{SD}} = 2.5 \text{ A}$, $dI_F/dt = 100 \text{ A}/\mu\text{s}$	—	190	—	ns
Q_{rr}	Reverse Recovery Charge	—	0.52	—	—	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

TYPICAL CHARACTERISTICS

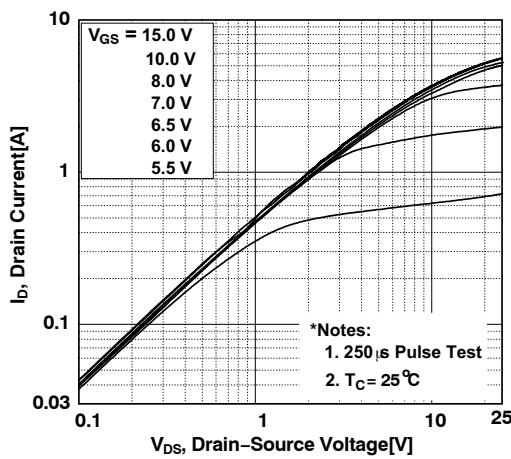


Figure 1. On-Region Characteristics

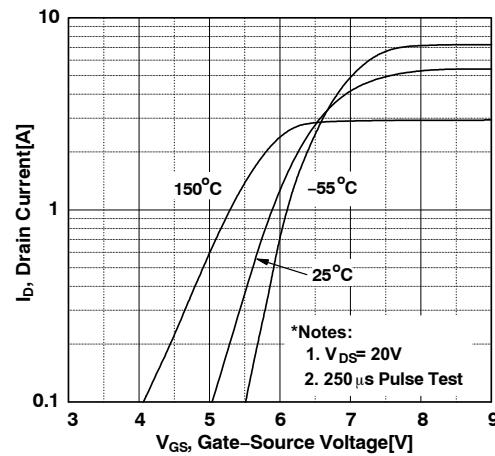


Figure 2. Transfer Characteristics

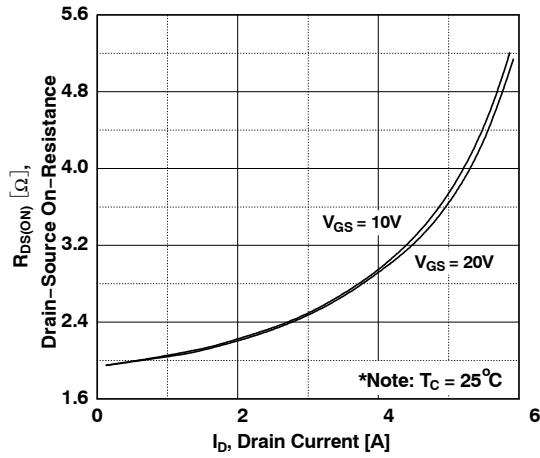


Figure 3. On-Resistance vs. Gate-to-Source Voltage

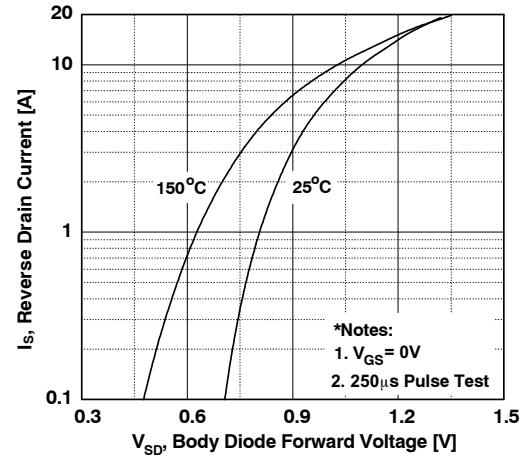


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

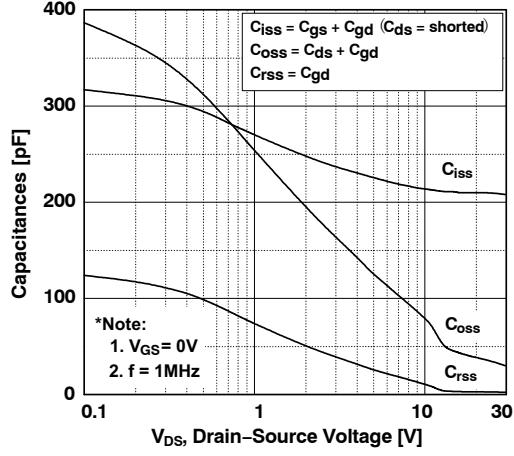


Figure 5. Capacitance Characteristics

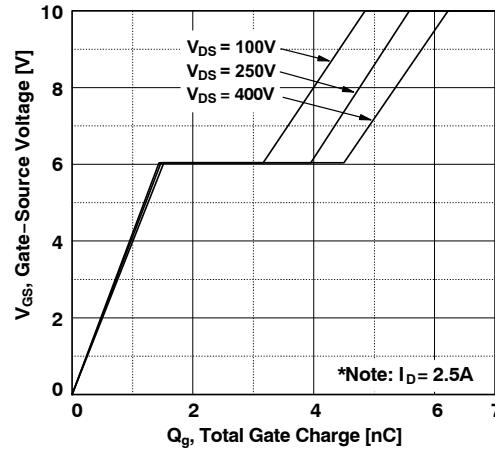
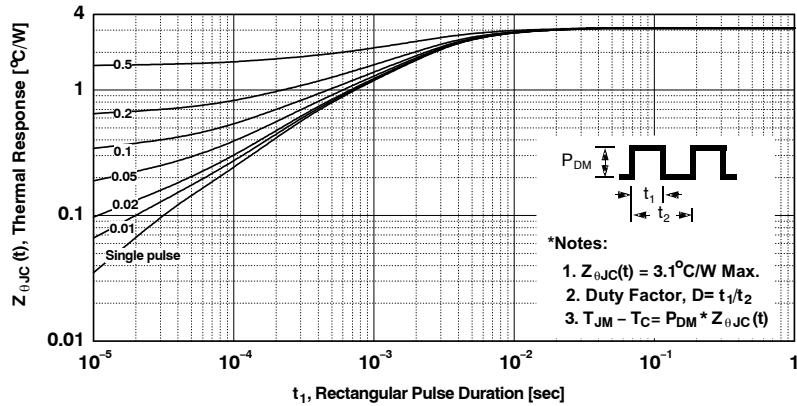
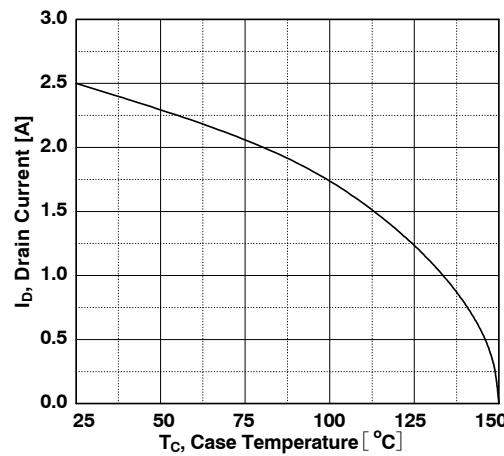
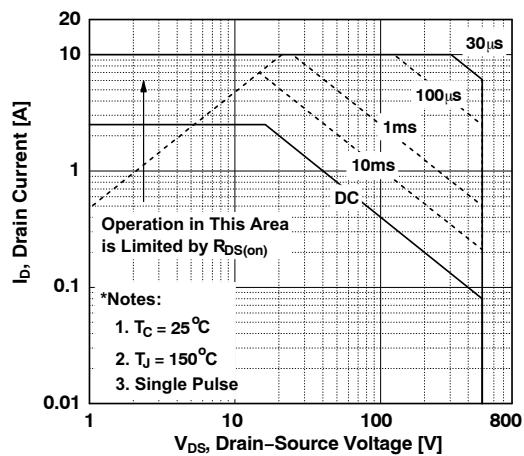
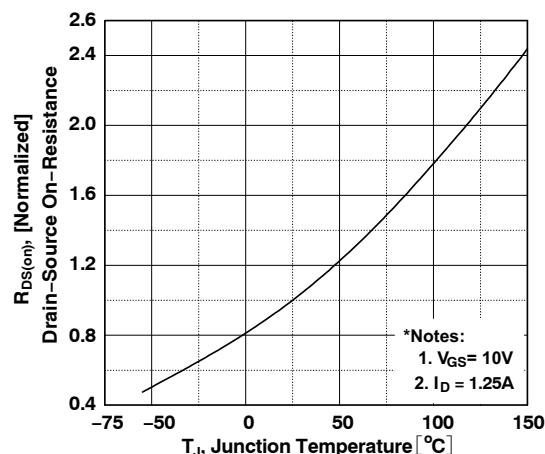
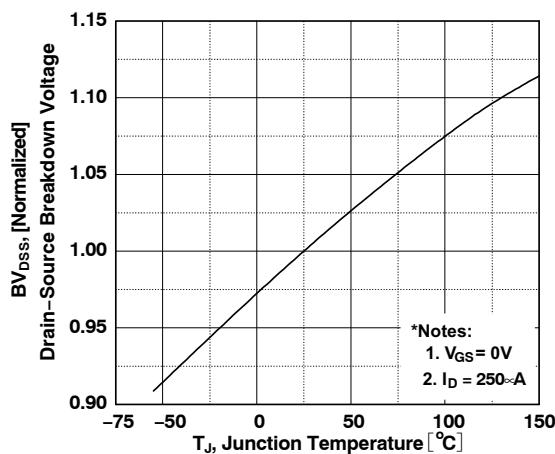


Figure 6. Gate Charge Characteristics

TYPICAL CHARACTERISTICS



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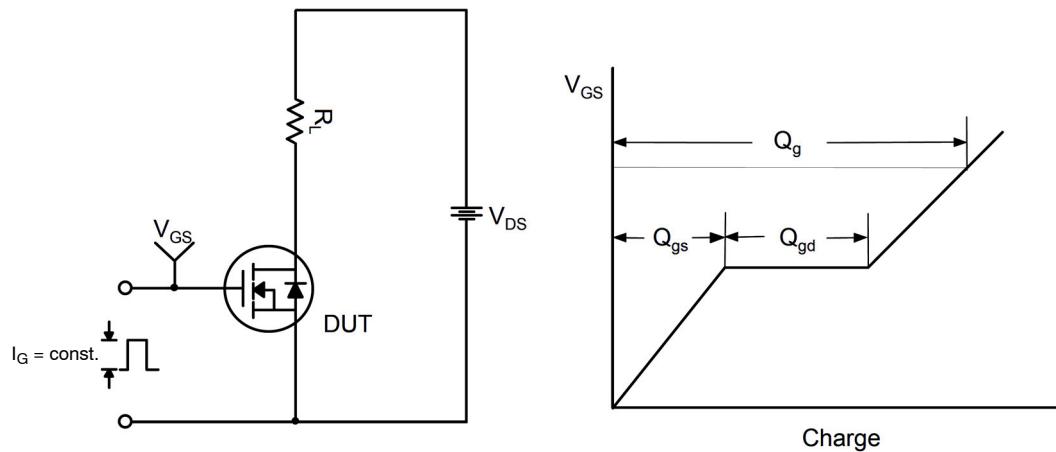


Figure 12. Gate Charge Test Circuit & Waveform

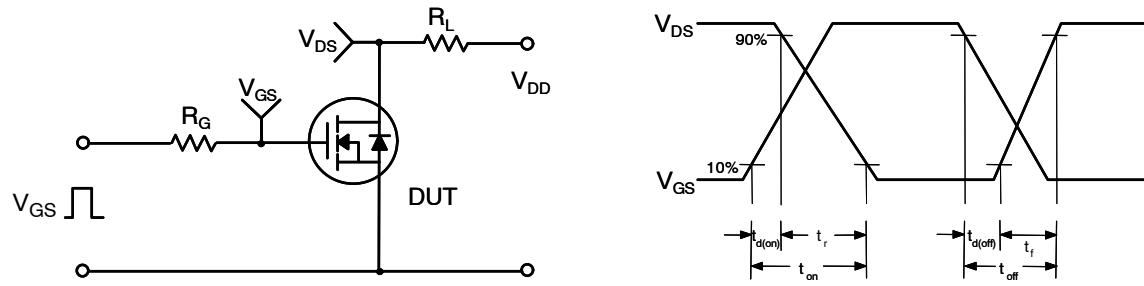


Figure 13. Resistive Switching Test Circuit & Waveforms

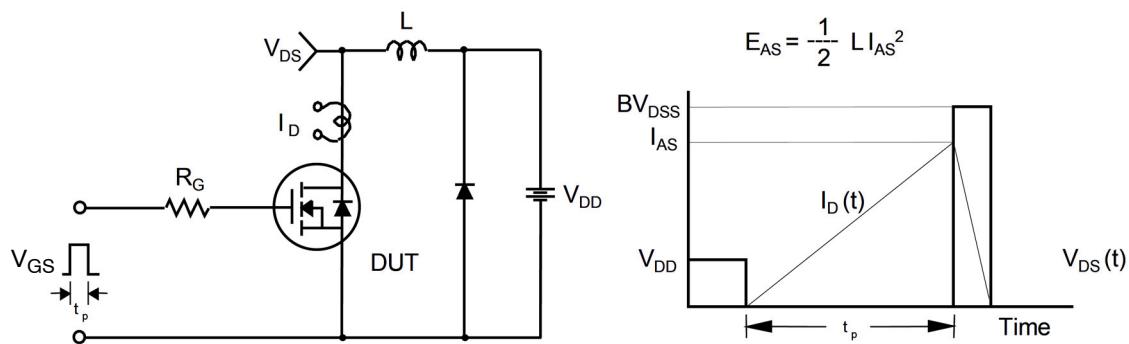


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

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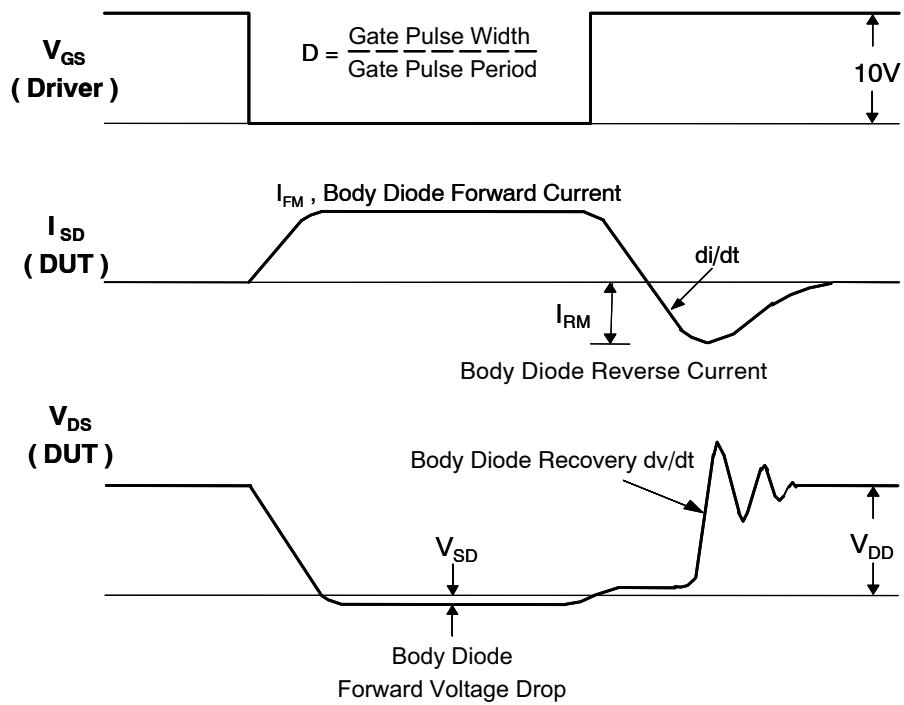
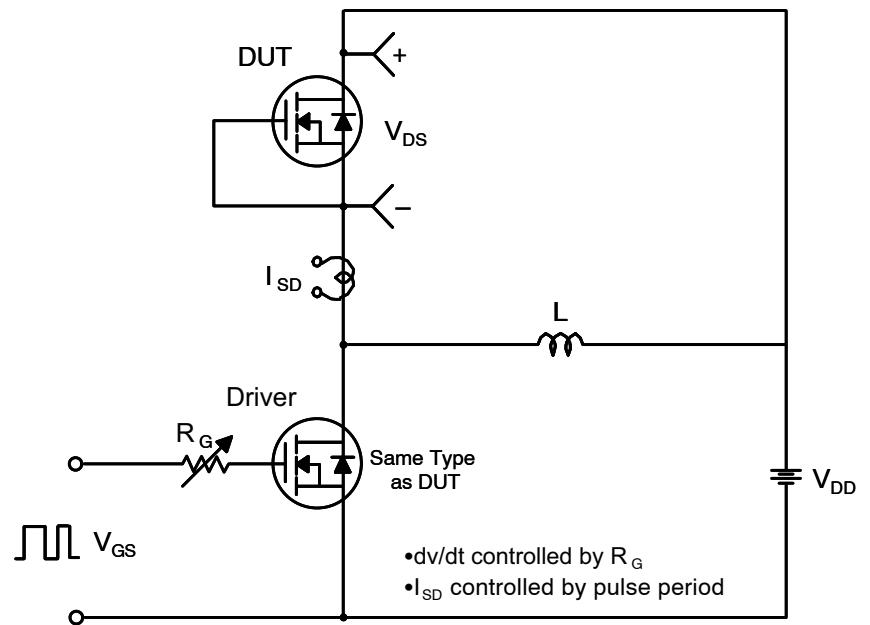
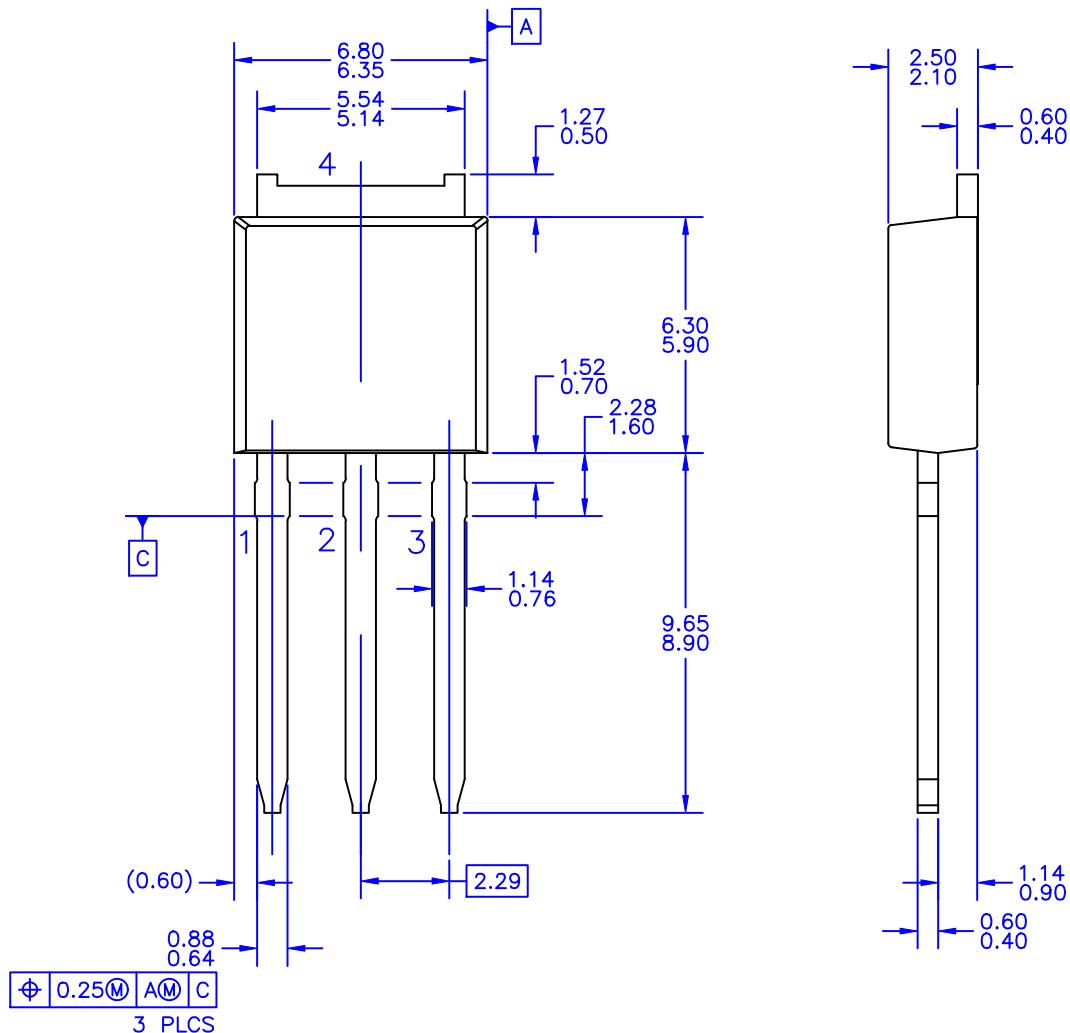


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

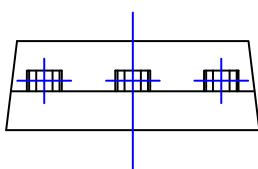
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CASE 369AR
ISSUE O

DATE 30 SEP 2016



NOTES: UNLESS OTHERWISE SPECIFIED

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